## **BGU7032**

# 1 GHz wideband low-noise amplifier with bypass Rev. 2 — 14 September 2010 Pro

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

The BGU7032 MMIC is a wideband amplifier with bypass mode. It is designed specifically for high linearity, low-noise applications over a frequency range of 40 MHz to 1 GHz. It is especially suited to Set-Top Box applications.

The LNA is housed in a 6-pin SOT363 plastic SMD package.

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

#### 1.2 Features and benefits

- Internally biased
- Programmable between G<sub>p</sub> = 10 dB and bypass
- Flat gain between 40 MHz and 1 GHz
- Noise figure of 4.5 dB
- High linearity with an IP3<sub>O</sub> of 29 dBm
- $\blacksquare$  75  $\Omega$  input and output impedance
- Power-down during bypass mode
- Bypass mode current consumption < 5 mA
- ESD protection > 2 kV Human Body Model (HBM) on all pins

#### 1.3 Applications

- Terrestrial and cable Set-Top Boxes (STB)
- Silicon and "Can" tuners
- Personal and Digital Video Recorders (PVR and DVR)
- Home networking and in-house signal distribution



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#### 1.4 Quick reference data

Table 1. Quick reference data

 $T_{amb}$  = 25 °C; typical values at  $V_{CC}$  = 5 V;  $Z_{S}$  =  $Z_{L}$  = 75  $\Omega$ ;  $R_{bias}$  = 43  $\Omega$ ; 40 MHz  $\leq$   $f_{1}$   $\leq$  1000 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled		4.75	5.0	5.25	V
I <sub>CC(tot)</sub>	total supply current	G <sub>p</sub> = 10 dB mode	[1]	-	43	-	mΑ
		bypass mode	[1]	-	4	-	mΑ
T <sub>amb</sub>	ambient temperature			-10	-	+70	°C
NF	noise figure	G <sub>p</sub> = 10 dB mode	<u>[1]</u>	-	4.5	-	dB
		bypass mode	[1]	-	2.5	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	1 GHz; $G_p = 10 \text{ dB}$ mode	<u>[1]</u>	-	14	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	G <sub>p</sub> = 10 dB mode	[1][2]	-	29	-	dBm

<sup>[1]</sup> Mode depends on setting of V<sub>CTRL</sub>; see <u>Table 8</u>.

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	RF_OUT	D. D. D.	
2	V <sub>CC</sub>	6 5 4	3 2
3	n.c.		6 — 1
4	CTRL	0	
5	GND	☐1 ☐2 ☐3	5 4 sym141
6	RF_IN		,

## 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BGU7032	-	plastic surface-mounted package; 6 leads	SOT363		

## 4. Marking

Table 4. Marking codes

Type number	Marking code
BGU7032	SD%

Note: % character indicates the location of production.

<sup>[2]</sup> The fundamental frequency ( $f_1$ ) is 1000 MHz. The intermodulation product (IM3) is  $2 \times f_2 - f_1$ , where  $f_2 = f_1 \pm 1$  MHz. Input power  $P_i = -10$  dBm.

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## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled		-0.6	5.25	V
V <sub>ctrl(Gp)</sub>	power gain control voltage	pin CTRL	[1]	0	$V_{CC}$	V
$I_{CC(tot)}$	total supply current			-	60	mΑ
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> ≤ 100 °C	[2]	-	250	mW
Pi	input power	single tone		-	10	dBm
T <sub>stg</sub>	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-10	+70	°C
V <sub>ESD</sub>	electrostatic discharge voltage	Human Body Model (HBM); according to JEDEC standard 22-A114E		2	-	kV

<sup>[1]</sup>  $V_{ctrl(Gp)}$  must not exceed  $V_{CC}$ ;  $I_{CTRL}$  must be limited to 5 mA (maximum).

**Remark:**  $V_{ctrl(Gp)}$  must not exceed  $V_{CC}$ ;  $I_{CTRL}$  must be limited to a maximum of 5 mA.

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		240	K/W

#### 7. Characteristics

Table 7. Characteristics

 $T_{amb}$  = 25 °C; typical values at  $V_{CC}$  = 5 V;  $Z_{S}$  =  $Z_{L}$  = 75  $\Omega$ ;  $R_{bias}$  = 43  $\Omega$ ; 40 MHz  $\leq$   $f_{1}$   $\leq$  1000 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled		4.75	5.0	5.25	V
I <sub>CC(tot)</sub>	total supply current	G <sub>p</sub> = 10 dB mode	[1]	-	43	-	mA
		bypass mode	[1]	-	4	-	mA
$ s_{21} ^2$	insertion power gain	G <sub>p</sub> = 10 dB mode	[1]	-	10	-	dB
		bypass mode	[1]	-	-2	-	dB
SL <sub>sl</sub>	slope straight line			-	-1	-	dB
FL	flatness of frequency response			-	-0.2	-	dB
NF	noise figure	G <sub>p</sub> = 10 dB mode	[1]	-	4.5	-	dB
		bypass mode	[1]	-	2.5	-	dB
$RL_{in}$	input return loss	G <sub>p</sub> = 10 dB mode	[1]	-	18	-	dB
		bypass mode	[1]	-	8	-	dB

<sup>[2]</sup>  $T_{sp}$  is the temperature at the solder point of the ground lead.

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 Table 7.
 Characteristics ...continued

 $T_{amb}$  = 25 °C; typical values at  $V_{CC}$  = 5 V;  $Z_{S}$  =  $Z_{L}$  = 75  $\Omega$ ;  $R_{bias}$  = 43  $\Omega$ ; 40 MHz  $\leq$   $f_{1}$   $\leq$  1000 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$RL_{out}$	output return loss	$G_p = 10 \text{ dB mode}$	[1]	-	12	-	dB
		bypass mode	[1]	-	8	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	1 GHz; $G_p = 10 \text{ dB}$ mode	[1]	-	14	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	G <sub>p</sub> = 10 dB mode	[1][2]	-	29	-	dBm
		bypass mode	[1][2]	-	29	-	dBm

<sup>[1]</sup> Mode depends on setting of  $V_{ctrl(Gp)}$  ( $V_{CTRL}$ ); see <u>Table 8</u>.

Table 8. Gain selection (pin CTRL)

-10 °C ≤  $T_{amb}$  ≤ +70 °C; recommended power-up condition:  $V_{CTRL}$  = logic 0 or < 0.7 V.

V <sub>ctrl(Gp)</sub> (V <sub>CTRL</sub> ) (V)	Mode
≤ 0.7	bypass
≥ 4.3	$G_p = 10 \text{ dB}$

Remark: V<sub>ctrl(Gp)</sub> must not exceed V<sub>CC</sub>; I<sub>CTRL</sub> must be limited to a maximum of 5 mA.

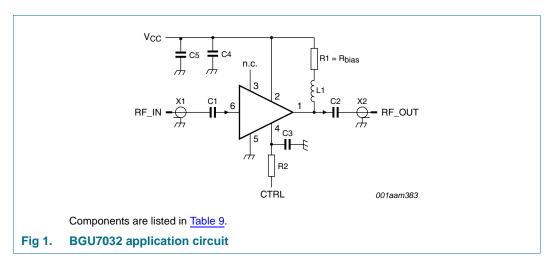
<sup>[2]</sup> The fundamental frequency ( $f_1$ ) is 1000 MHz. The intermodulation product (IM3) is  $2 \times f_2 - f_1$ , where  $f_2 = f_1 \pm 1$  MHz. Input power  $P_i = -10$  dBm.

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## 8. Application information

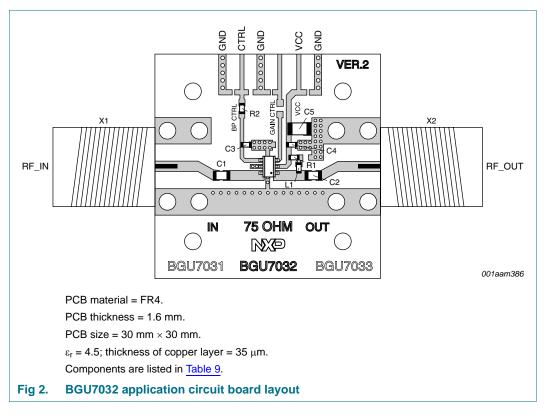
Other applications are possible. Please contact your local sales representative for more information. Application notes are available on the NXP website.

#### 8.1 Application circuit



All control and supply lines must be decoupled properly. The decoupling capacitors must be placed as close to the device as possible.

#### 8.2 Application circuit board layout



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Table 9.List of componentsSee Figure 1 and Figure 2.

Component	Description	Value	Remarks	Function
C1, C2	capacitor	10 nF		DC blocking
C3, C4	capacitor	10 nF		decoupling
C5	capacitor	10 μF		decoupling
L1	chip ferrite bead	$1.5~\mathrm{k}\Omega$	Murata BLM18HE152SN1DF	RF choke
R1	resistor	43 Ω	[1] R <sub>bias</sub>	bias setting
R2	resistor	$1.8~\mathrm{k}\Omega$		current limiting
X1, X2	connector	75 Ω	F-connector, edge mount PCB reflow type, Bomar 861V509ERG	input/output

<sup>[1]</sup> L1 and R1 must have a power rating of 0.1 W or higher.

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## Package outline

#### Plastic surface-mounted package; 6 leads

**SOT363** 

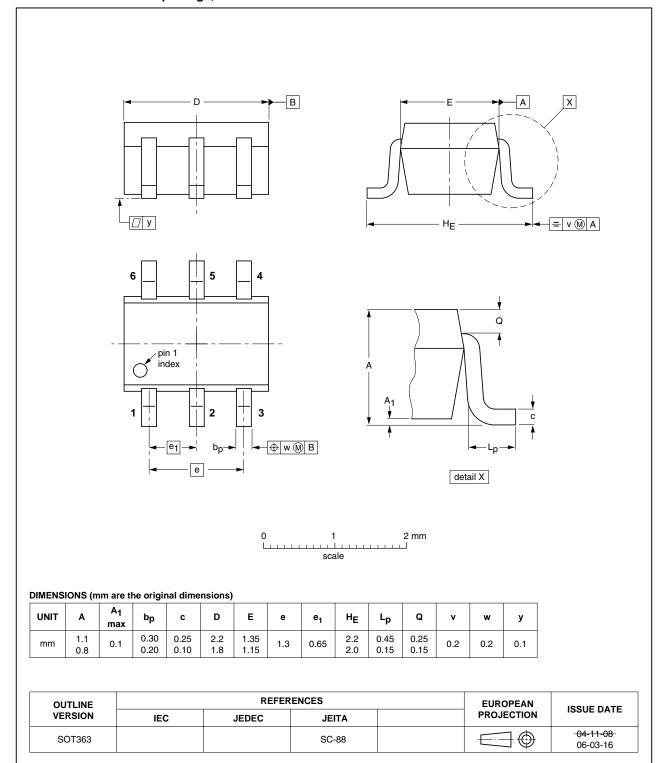


Fig 3. Package outline SOT363

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## 10. Abbreviations

Table 10. Abbreviations

Acronym	Description
AC	Alternating Current
DC	Direct Current
LNA	Low-Noise Amplifier
MMIC	Monolithic Microwave Integrated Circuit
PCB	Printed-Circuit Board
RF	Radio Frequency
SMD	Surface-Mounted Device

## 11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BGU7032 v.2	20100914	Product data sheet	-	BGU7032 v.1	
Modifications:  • The status of this data sheet has been changed to Product data sheet.					
BGU7032 v.1	20100817	Preliminary data sheet	-	-	

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#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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